SILICON (Si) POWER MOSFET $\boldsymbol{\Delta}$ CEB140N10


## CEB140N10

## $100 \mathrm{~V} \Delta 6.1 \mathrm{~m} \Omega \triangle 137 \mathrm{~A} \triangle$ Si MOSFET

SILICON Si MOSFET $\triangle$ SMD type
N -channel enhancement mode UL94V-0 rated flame retardant epoxy

TO263 (D2PAK) package $\boldsymbol{\Delta}$ MSL 3
Super high dense cell density for extremely low $\mathrm{R}_{\mathrm{DS}(\mathrm{ON})}$ High power and current handling capability

## MAXIMUM RATINGS

| Parameter ( $\mathrm{T}_{\mathrm{C}}=25^{\circ} \mathrm{C}$, unless otherwise noted) |  | Characteristics |
| :---: | :---: | :---: |
| Drain-Source Voltage | $\mathrm{V}_{\text {DS }}$ | 100V |
| Gate-Source Voltage | $\mathrm{V}_{\text {GS }}$ | $\pm 20 \mathrm{~V}$ |
| Continuous Drain Current at $\mathrm{T}_{\mathrm{c}}=25^{\circ} \mathrm{C}$ | ID | 137A |
| Continuous Drain Current at $\mathrm{T}_{\mathrm{C}}=100^{\circ} \mathrm{C}$ | ID | 87A |
| Pulsed Drain Current ${ }^{\text {Note } 1}$ | IDM | 548A |
| Maximum Power Dissipation at $\mathrm{T}_{\mathrm{C}}=25^{\circ} \mathrm{C}$ | $\mathrm{PD}_{\mathrm{D}}$ | 208W |
| Power Dissipation Derating above $25^{\circ} \mathrm{C}$ | $\Delta \mathrm{P}_{\mathrm{D}}$ | $1.7 \mathrm{~W} /{ }^{\circ} \mathrm{C}$ |
| Single Pulsed Avalanche Energy ${ }^{\text {Note } 4}$ | EAS | 800 mJ |
| Single Pulsed Avalanche Current ${ }^{\text {Note } 4}$ | $\mathrm{I}_{\text {AS }}$ | 40A |
| Operating and Storage Temperature Range | $\mathrm{T}_{\mathrm{J}}, \mathrm{T}_{\text {STG }}$ | $-55^{\circ} \mathrm{C}$ to $+150^{\circ} \mathrm{C}$ |

## THERMAL CHARACTERISTICS

| Parameter | Symbol | Limit |
| :--- | :---: | :--- |
| Thermal Resistance, Junction-to-Case | $\mathbf{R}_{\text {TH_」c }}$ | $0.6^{\circ} \mathrm{C} / \mathrm{W}$ |
| Thermal Resistance, Junction-to-Ambient ${ }^{\text {Note 2 }}$ | $\mathbf{R}_{\text {TH_JA }}$ | $62.5^{\circ} \mathrm{C} / \mathrm{W}$ |

## APPLICATIONS

| Battery Management <br> Systems | E-Bike | Industrial <br> Control | Power <br> Inverter | UPS |
| :---: | :---: | :---: | :---: | :---: |

## PIN DESCRIPTION

| Circuit Diagram | Outline - Bottom View | Pin No. | Description |
| :---: | :---: | :---: | :---: |
|  |  | $\begin{aligned} & 1 \\ & 2 \\ & 3 \end{aligned}$ | Drain Source Gate |
| MGT $\Delta$ Manufacturer Group of Technology |  |  |  |

CEB140N10 ^ Rev. 001 ^ Date: 30/09/2022 ^ Page: 1
Copyright by MGT $\boldsymbol{\Delta}$ www.mgt.co.com $\boldsymbol{\Delta}$ All rights reserved $\boldsymbol{\Delta}$ The information in this document is subject to change without notice.

ELECTRICAL CHARACTERISTICS $\triangle \mathrm{T}_{\mathrm{C}}=25^{\circ} \mathrm{C}$, unless otherwise noted

| Item | Condition | Symbol | Min. | Typ. | Max. | Unit |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| Off Characteristics |  |  |  |  |  |  |
| Drain-Source Breakdown Voltage | $\mathrm{V}_{G S}=0 \mathrm{~V}, \mathrm{I}_{\mathrm{D}}=250 \mu \mathrm{~A}$ | BV ${ }_{\text {DSS }}$ | 100 |  |  | V |
| Zero Gate Voltage Drain Current | $\mathrm{V}_{\text {DS }}=100 \mathrm{~V}, \mathrm{~V}_{\mathrm{GS}}=0 \mathrm{~V}$ | loss |  |  | 1 | $\mu \mathrm{A}$ |
| Gate Body Leakage Current, Forward | $V_{G S}=20 \mathrm{~V}, \mathrm{~V}_{\mathrm{DS}}=0 \mathrm{~V}$ | IGSSF |  |  | 100 | nA |
| Gate Body Leakage Current, Reverse | $V_{G S}=-20 \mathrm{~V}, \mathrm{~V}_{\text {DS }}=0 \mathrm{~V}$ | $\mathrm{I}_{\text {GSSR }}$ |  |  | -100 | nA |
| On Characteristics Note 3 |  |  |  |  |  |  |
| Gate Threshold Voltage | $V_{G S}=V_{D S}, I_{D}=250 \mu \mathrm{~A}$ | $V_{\text {GS(th) }}$ | 2 |  | 4 | V |
| Static Drain-Source On-Resistance | $V_{G S}=10 \mathrm{~V}, \mathrm{I}_{\mathrm{D}}=35 \mathrm{~A}$ | R $\mathrm{DS}_{(\text {ON })}$ |  | 6.1 | 7.5 | $\mathrm{m} \Omega$ |
| Dynamic Characteristics Note 3 |  |  |  |  |  |  |
| Input Capacitance | $\mathrm{V}_{\mathrm{DS}}=25 \mathrm{~V}, \mathrm{~V}_{\mathrm{GS}}=0 \mathrm{~V}, \mathrm{f}=800 \mathrm{kHz}$ | $\mathrm{C}_{15 s}$ |  | 6650 |  | pF |
| Output Capacitance | $\mathrm{V}_{\mathrm{DS}}=25 \mathrm{~V}, \mathrm{~V}_{\mathrm{GS}}=0 \mathrm{~V}, \mathrm{f}=800 \mathrm{kHz}$ | Coss |  | 605 |  | pF |
| Reverse Transfer Capacitance | $\mathrm{V}_{\mathrm{DS}}=25 \mathrm{~V}, \mathrm{~V}_{\mathrm{GS}}=0 \mathrm{~V}, \mathrm{f}=800 \mathrm{kHz}$ | CRSS |  | 495 |  | pF |
| Switching Characteristics ${ }^{\text {Note } 3}$ |  |  |  |  |  |  |
| Turn-On Delay Time | $V_{D D}=50 \mathrm{~V}, \mathrm{~V}_{G S}=10 \mathrm{~V}, \mathrm{I}_{\mathrm{D}}=70 \mathrm{~A}, \mathrm{R}_{G(\text { ext }}=2.5 \Omega$ | $\mathrm{t}_{\mathrm{D} \text { (ON) }}$ |  | 44 |  | ns |
| Turn-On Rise Time | $V_{D D}=50 \mathrm{~V}, \mathrm{~V}_{G S}=10 \mathrm{~V}, \mathrm{I}_{\mathrm{D}}=70 \mathrm{~A}, \mathrm{R}_{G(\text { (ext }}=2.5 \Omega$ | $t_{R}$ |  | 23 |  | ns |
| Turn-Off Delay Time | $V_{D D}=50 \mathrm{~V}, \mathrm{~V}_{G S}=10 \mathrm{~V}, \mathrm{I}_{\mathrm{D}}=70 \mathrm{~A}, \mathrm{R}_{G(\text { ext })}=2.5 \Omega$ | $\mathrm{t}_{\text {(OFF) }}$ |  | 98 |  | ns |
| Turn-Off Fall Time | $V_{D D}=50 \mathrm{~V}, \mathrm{~V}_{G S}=10 \mathrm{~V}, \mathrm{I}_{\mathrm{D}}=70 \mathrm{~A}, \mathrm{R}_{G(\text { (ext }}=2.5 \Omega$ | $\mathrm{t}_{\mathrm{F}}$ |  | 27 |  | ns |
| Total Gate Charge | $V_{D D}=80 \mathrm{~V}, \mathrm{~V}_{G S}=10 \mathrm{~V}, \mathrm{I}_{\mathrm{D}}=70 \mathrm{~A}$ | $\mathrm{Q}_{\text {G }}$ |  | 231 |  | nC |
| Gate Source Charge | $V_{D D}=80 \mathrm{~V}, V_{G S}=10 \mathrm{~V}, \mathrm{I}_{\mathrm{D}}=70 \mathrm{~A}$ | $\mathrm{Q}_{\text {GS }}$ |  | 63 |  | nC |
| Gate Drain Charge | $V_{D D}=80 \mathrm{~V}, \mathrm{~V}_{G S}=10 \mathrm{~V}, \mathrm{I}_{\mathrm{D}}=70 \mathrm{~A}$ | $\mathrm{Q}_{\text {GD }}$ |  | 70 |  | nC |
| Drain-Source Diode Characteristics and Maximum Ratings |  |  |  |  |  |  |
| Drain-Source Diode Forward Current |  | Is |  |  | 137 | A |
| Drain-Source Diode Forward Voltage Note 2 | $\mathrm{V}_{\mathrm{GS}}=0 \mathrm{~V}, \mathrm{I}_{\mathrm{S}}=35 \mathrm{~A}$ | $\mathrm{V}_{\text {SD }}$ |  |  | 1.5 | V |

## Notes

1: Repetitive Rating: Pulse width limited by maximum junction temperature
2: Pulse Test: Pulse Width $\leq \mathbf{3 0 0} \mu \mathrm{s}$, Duty Cycle $\leq \mathbf{2 \%}$.
3: Guaranteed by design, not subject to production testing.
4: $\quad L=1 \mathrm{mH}, \mathrm{I}_{\mathrm{AS}}=40 \mathrm{~A}, \mathrm{~V}_{\mathrm{DD}}=25 \mathrm{~V}, \mathrm{R}_{\mathrm{G}}=25 \Omega$, Starting $\mathrm{T}_{\mathrm{J}}=25^{\circ} \mathrm{C}$

SILICON (Si) POWER MOSFET $\triangle$ CEB140N10

REFERENCE DATA ^ TYPICAL DEVICE PERFORMANCE


SILICON (Si) POWER MOSFET $\triangle$ CEB140N10

REFERENCE DATA $\triangle$ TYPICAL DEVICE PERFORMANCE


Fig. 11 - Switching Test Circuit


Square Wave Pulse Duration (msec)

## PART MARKING

## DATE CODE



Example: 11S4Z

Coding list for „Day"
Coding list for „Month"

| $\mathbf{1}$ | $\mathbf{2}$ | $\mathbf{3}$ | $\mathbf{4}$ | $\mathbf{5}$ | $\mathbf{6}$ | $\mathbf{7}$ | $\mathbf{8}$ | $\mathbf{9}$ | $\mathbf{A}$ |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| 01 | 02 | 03 | 04 | 05 | 06 | 07 | 08 | 09 | 10 |
| $\mathbf{B}$ | $\mathbf{C}$ | $\mathbf{D}$ | $\mathbf{E}$ | $\mathbf{F}$ | $\mathbf{G}$ | $\mathbf{H}$ | $\mathbf{I}$ | $\mathbf{J}$ | $\mathbf{K}$ |
| 11 | 12 | 13 | 14 | 15 | 16 | 17 | 18 | 19 | 20 |
| $\mathbf{L}$ | $\mathbf{M}$ | $\mathbf{N}$ | $\mathbf{O}$ | $\mathbf{P}$ | $\mathbf{Q}$ | $\mathbf{R}$ | $\mathbf{S}$ | $\mathbf{T}$ | $\mathbf{U}$ |
| 21 | 22 | 23 | 24 | 25 | 26 | 27 | 28 | 29 | 30 |
| $\mathbf{V}$ |  |  |  |  |  |  |  |  |  |
| 31 |  |  |  |  |  |  |  |  |  |


| $\mathbf{1}$ | $\mathbf{2}$ | $\mathbf{3}$ | $\mathbf{4}$ | $\mathbf{5}$ | $\mathbf{6}$ |
| :---: | :---: | :---: | :---: | :---: | :---: |
| Jan | Feb | Mar | Apr | May | Jun |
| $\mathbf{7}$ | $\mathbf{8}$ | $\mathbf{9}$ | $\mathbf{A}$ | $\mathbf{B}$ | $\mathbf{C}$ |
| Jul | Aug | Sep | Oct | Nov | Dec |

Coding list for „Year"

| $\mathbf{0}$ | $\mathbf{1}$ | $\mathbf{2}$ | $\mathbf{3}$ | $\mathbf{4}$ |
| :---: | :---: | :---: | :---: | :---: |
| 2020 | 2021 | 2022 | 2023 | 2024 |
| $\mathbf{5}$ | $\mathbf{6}$ | $\mathbf{7}$ | $\mathbf{8}$ | $\mathbf{9}$ |
| 2025 | 2026 | 2027 | 2028 | 2029 |

## PACKAGE OUTLINE



| Sym | Millimeters <br> (Min.) | Millimeters <br> (Typ.) | Millimeters <br> (Max.) |  | Sym | Millimeters <br> (Min.) | Millimeters <br> (Typ.) | Millimeters <br> (Max.) |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| A | 4.37 | 4.57 | 4.77 | E | 9.86 | 10.16 | 10.36 |  |
| A1 | 1.22 | 1.27 | 1.42 | E5 | 7.06 | - | - |  |
| A2 | 2.49 | 2.69 | 2.89 | e |  | 2.54 BSC |  |  |
| A3 | 0.00 | 0.13 | 0.25 | H | 14.70 | 15.10 | 15.50 |  |
| b | 0.70 | 0.81 | 0.96 | H2 | 1.07 | 1.27 | 1.47 |  |
| b1 | 1.17 | 1.27 | 1.47 | L | 2.00 | 2.30 | 2.60 |  |
| c | 0.30 | 0.38 | 0.53 | L1 | 1.40 | 1.55 | 1.70 |  |
| D1 | 8.50 | 8.70 | 8.90 | L4 |  | 0.25 BSC |  |  |
| D4 | 6.60 | - | - |  |  | $0^{\circ}$ | $5^{\circ}$ | $9^{\circ}$ |

ORDERING INFORMATION

| Part Number | Package | Packing | Reel Qty. | Inner Box Qty. | Outer Box Qty. |
| :---: | :---: | :---: | :---: | :---: | :---: |
| CEB140N10 | TO263 (D2PAK) | Reel | 800 pcs | 800 pcs | 6,400 pcs |

RECOMMENDED PAD LAYOUT


| Sym | Millimeters <br> (Min.) | Millimeters <br> (Typ.) | Millimeters <br> (Max.) | Sym | Millimeters <br> (Min.) | Millimeters <br> (Typ.) | Millimeters <br> (Max.) |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| F1 | - | 12.20 | - | F5 | - | 2.54 | - |
| F2 | - | 16.90 | - | F6 | - | 1.60 | - |
| F3 | - | 2.54 | - | F7 | - | 9.75 | - |
| F4 | - |  |  |  | - |  |  |

## Notes:

1. The suggested land pattern dimensions have been provided for reference only.
2. For further information, please reference document IPC-7351A.

SILICON (Si) POWER MOSFET - CEB140N10

REEL DIMENSIONS $\boldsymbol{\wedge}$ All dimensions in mm


| Tape Size | Reel Size | $\mathbf{M}$ | $\mathbf{N}$ | $\mathbf{T}$ | $\mathbf{H}$ | $\mathbf{K}$ | $\mathbf{S}$ |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| 24 mm |  | $\varnothing 330$ | $\varnothing 330.00$ | $\varnothing 100.00$ | 2.10 | 22.00 | 13.00 |

TAPE DIMENSIONS $\triangle$ All dimensions in mm


| Package | AO | B0 | K0 | D0 | D1 | E | E1 | E2 | P0 | P1 | P2 | T |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| TO263 | 10.80 | 16.30 | 4.85 | 1.50 | 1.55 | 24.00 | 1.75 | 11.50 | 16.00 | 4.00 | 2.00 | 0.35 |
| (D²PAK) | $\pm 0.10$ | $\pm 0.10$ | $\pm 0.10$ | $\pm 0.10$ | $\pm 0.05$ | $\pm 0.30$ | $\pm 0.10$ | $\pm 0.10$ | $\pm 0.10$ | $\pm 0.10$ | $\pm 0.10$ | $\pm 0.05$ |

Note: All dimensions meet EIA-481-D requirements.

SILICON (Si) POWER MOSFET $\Delta$ CEB140N10

## RECOMMENDED REFLOW SOLDERING PROFILE



## Recommended reflow soldering conditions $\triangle$ Refer to JEDEC J-STD-020E

| Profile Features |  | Sn-Pb Eutetic Assembly | Pb-Free Assembly |
| :---: | :---: | :---: | :---: |
| Preheat temperature min. | $T_{s \text { min }}$ | $100{ }^{\circ} \mathrm{C}$ | $150{ }^{\circ} \mathrm{C}$ |
| Preheat temperature max. | $\mathrm{T}_{\text {s max }}$ | $150{ }^{\circ} \mathrm{C}$ | $200^{\circ} \mathrm{C}$ |
| Preheat time $\mathrm{t}_{s}$ from $\mathrm{T}_{\text {s min }}$ to $\mathrm{T}_{\text {s max }}$ | $\mathrm{t}_{\text {s }}$ | 120 seconds | 120 seconds |
| Ramp-up rate ( $\mathrm{T}_{\mathrm{L}}$ to $\mathrm{T}_{\mathrm{p}}$ ) |  | max. $3^{\circ} \mathrm{C} /$ second | max. $3^{\circ} \mathrm{C} /$ second |
| Liquidous temperature | $\mathrm{T}_{\mathrm{L}}$ | $183{ }^{\circ} \mathrm{C}$ | $217{ }^{\circ} \mathrm{C}$ |
| Time $t_{L}$ maintained above $\mathrm{T}_{\mathrm{L}}$ | $\mathrm{t}_{\mathrm{L}}$ | 150 seconds max. | 150 seconds max. |
| Peak package body temperature | Tp | $235^{\circ} \mathrm{C}$ | $260^{\circ} \mathrm{C}$ |
| Timeframe of within $5^{\circ} \mathrm{C}$ below and up to max actual peak body temperature | $\mathrm{t}_{\mathrm{p}}$ | 20 seconds max. | 30 seconds max. |
| Ramp-down rate ( $\mathrm{L}_{\mathrm{L}}$ to $\mathrm{T}_{\mathrm{p}}$ ) |  | max. $6^{\circ} \mathrm{C} /$ second | max. $6^{\circ} \mathrm{C} /$ second |
| Time $25^{\circ} \mathrm{C}$ to peak temperature |  | max. 6 minutes | max. 8 minutes |

## REVISION TABLE

| Revision | Date | Status | Notes |
| :--- | :--- | :--- | :--- |
| 001 | $30 / 09 / 2022$ | Initial release | Initial publication |
|  |  |  |  |
|  |  |  |  |
|  |  |  |  |
|  |  |  |  |
|  |  |  |  |

## DISCLAIMER

Except for the written expressed warranties, MGT does not implicitly, by assumption or whatever else, warrant, under-take, promise any other warranty or guaranty for any MGT product.

All information and technical specifications made available by MGT are for guidance only and we reserve the right to change or modify them without prior notice. Unless expressly stated in writing by MGT, we reject any guarantees, obligations, or warranties.

All MGT products with the technical specifications described are suitable for use in certain applications. Operating, production, storage and environmental conditions can have a massive influence on the parameters mentioned in the data sheets, which cause the performance to vary over time.

It is subject to the user's duty of care to design and validate his products in such a way that appropriate measures are taken, such as protective circuits or redundant systems to ensure the safety standards required in the application.

MGT components are not designed or rated for use in life support, rescue, safety critical, military, or aerospace applications where failure or malfunction could result in property or environmental damage, serious injury or death. In the aforementioned cases, please contact us before using MGT products.

In principle, we reserve all rights and MGT's general terms and conditions apply. You can find them on our website www.mgt.co.com.

